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Aixtron Crius 31x2” MOCVD
SN 1001 700373 Vintage 09/2008
Currently in 2” Configuration

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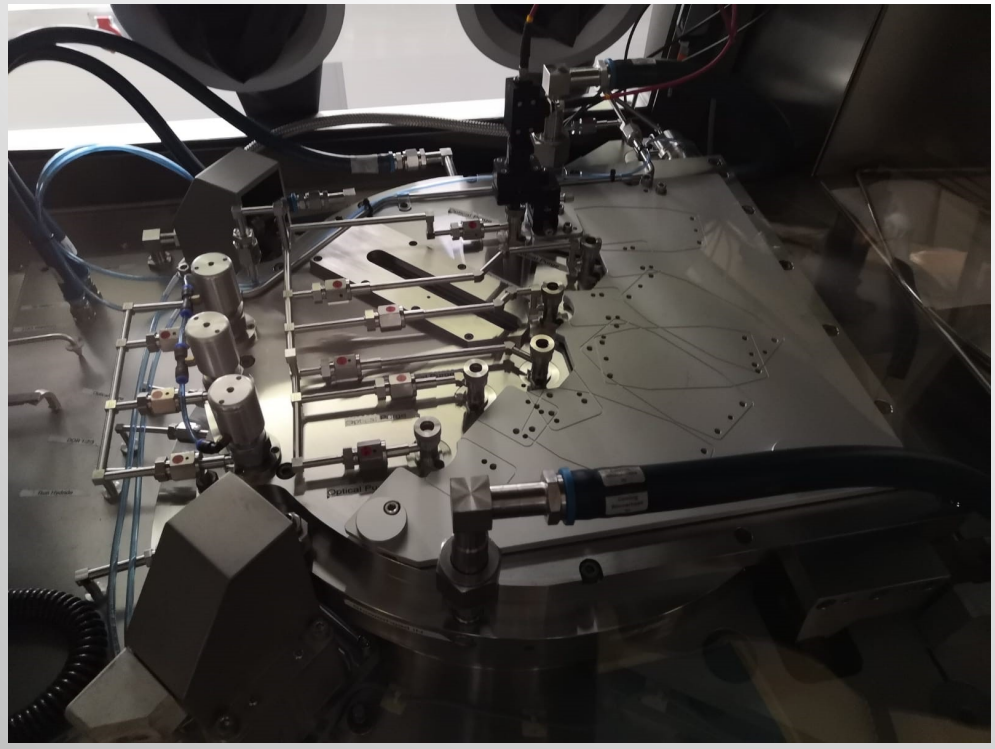

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Process specification in current configuration

GaN	Growth rate r =2 to 3 µm/h Thickness uniformity σ ≤ 3% Threading dislocation density on the surface ρTD < 3e8 cm-2 @ thickness 4 µm
n-GaN:Si	n ≥ 1e18 cm-3 Mobility µ ≥ 300 cm2/Vs @ n = 1e18 cm-3 Doping uniformity σ ≤ 10%
p-GaN:Mg	p ≥ 5e17 cm-3 Resistivity ρ ≤ 2Ωcm Doping uniformity σ ≤ 10%
AlGaN	Al-composition up to 20% Al-composition uniformity σ < 8% of absolute value Growth rate r = 1 to 1.5 µm/h
n-AlGaN:Si	n ≥ 1e18 cm-3
p-AlGaN:Mg	p ≥ 1e17 cm-3
InGaN/GaN MQW	1. Wavelength 470 ± 10 nm 2. Wavelength 520 ± 10 nm Wavelength uniformity σ ≤ 1%
AlGaN/GaN superlattice	Al-composition up to 40%

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- **Equipment Support**
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- **Process Support**
  Process design, Improvement,
  Fab-to-Fab Transfer and Integration

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